

RADIATION HARDENED N-CHANNEL MOSFET

Reference MIL-PRF-19500/601

DEVICES

2N7262 2N7262U

LEVELS

**JANSR (100K RAD(Si))
 JANSF (300K RAD(Si))**

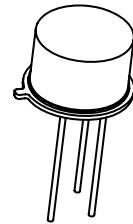
ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	200	Vdc
Gate – Source Voltage	V_{GS}	± 20	Vdc
Continuous Drain Current $T_C = +25^\circ\text{C}$	I_{D1}	5.5	A _{dc}
Continuous Drain Current $T_C = +100^\circ\text{C}$	I_{D2}	3.5	A _{dc}
Max. Power Dissipation	P_{tl}	25 ⁽¹⁾	W
Drain to Source On State Resistance	$R_{ds(on)}$	0.35 ⁽²⁾	Ω
Operating & Storage Temperature	T_{op}, T_{stg}	-55 to +150	$^\circ\text{C}$

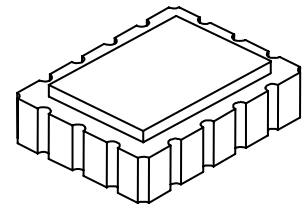
Note: (1) Derated Linearly by 0.2 W/ $^\circ\text{C}$ for $T_C > +25^\circ\text{C}$
 (2) $V_{GS} = 12\text{Vdc}$, $I_D = 3.5\text{A}$

PRE-IRRADIATION ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Drain-Source Breakdown Voltage $V_{GS} = 0\text{V}$, $I_D = 1\text{mA}$	$V_{(BR)DSS}$	200		Vdc
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}$, $I_D = 1.0\text{mA}$ $V_{DS} \geq V_{GS}$, $I_D = 1.0\text{mA}$, $T_j = +125^\circ\text{C}$ $V_{DS} \geq V_{GS}$, $I_D = 1.0\text{mA}$, $T_j = -55^\circ\text{C}$	$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	Vdc
Gate Current $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$ $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$, $T_j = +125^\circ\text{C}$	I_{GSS1} I_{GSS2}		± 100 ± 200	nA _{dc}
Drain Current $V_{GS} = 0\text{V}$, $V_{DS} = 160\text{V}$ $V_{GS} = 0\text{V}$, $V_{DS} = 200\text{V}$, $T_j = +125^\circ\text{C}$ $V_{GS} = 0\text{V}$, $V_{DS} = 160\text{V}$, $T_j = +125^\circ\text{C}$	I_{DSS1} I_{DSS2} I_{DSS3}		25 1.0 0.25	μA _{dc} mA _{dc} mA _{dc}
Static Drain-Source On-State Resistance $V_{GS} = 12\text{V}$, $I_D = 3.5\text{A}$ pulsed $V_{GS} = 12\text{V}$, $I_D = 5.5\text{A}$ pulsed $T_j = +125^\circ\text{C}$ $V_{GS} = 12\text{V}$, $I_D = 3.5\text{A}$ pulsed	$r_{DS(on)1}$ $r_{DS(on)2}$ $r_{DS(on)3}$		0.350 0.364 0.60	Ω Ω Ω
Diode Forward Voltage $V_{GS} = 0\text{V}$, $I_D = 5.5\text{A}$ pulsed	V_{SD}		1.4	Vdc



**TO-205AF
 (modified TO-39)
 JANSR2N7262, JANSF2N7262
 See Figure 1**



**18 PIN LEADLESS CHIP CARRIER
 JANSR2N7262U, JANSF2N7262U
 See Figure 2**

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DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate Charge:				
On-State Gate Charge	$Q_{g(on)}$		50	nC
Gate to Source Charge	Q_{gs}		10	
Gate to Drain Charge	Q_{gd}		20	
$V_{GS} = 12V, I_D = 5.5A$ $V_{DS} = 100V$				

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Switching time tests:				
Turn-on delay time	$t_{d(on)}$		25	ns
Rinse time	t_r		32	
Turn-off delay time	$t_{d(off)}$		40	
Fall time	t_f		40	
Diode Reverse Recovery Time	t_{rr}		400	ns
$I_D = 5.5A, V_{GS} = 12Vdc,$ Gate drive impedance = 2.35 $\Omega,$ $V_{DD} = 100Vdc$				
$di/dt \leq 100A/\mu s, V_{DD} \leq 30V,$ $I_F = 5.5A$				

POST-IRRADIATION ELECTRICAL CHARACTERISTICS (3) ($T_A = +25^\circ C$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Drain-Source Breakdown Voltage $V_{GS} = 0V, I_D = 1mA_{dc}$	$V_{(BR)DSS}$	200		Vdc
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}, I_D = 1.0mA$ MSR $V_{DS} \geq V_{GS}, I_D = 1.0mA$ MSF	$V_{GS(th)1}$ $V_{GS(th)1}$	2.0 1.25	4.0 4.5	Vdc
Gate Current $V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS1}		± 100	nA _{dc}
Drain Current $V_{GS} = 0V, V_{DS} = 160V$ MSR $V_{GS} = 0V, V_{DS} = 160V$ MSF	I_{DSS1}		25 50	μA_{dc}
Static Drain-Source On-State Voltage $V_{GS} = 12V, I_D = 3.5A$ pulsed MSR $V_{GS} = 12V, I_D = 3.5A$ pulsed MSF	$V_{DS(on)}$		1.225 1.68	Vdc
Diode Forward Voltage $V_{GS} = 0V, I_D = 5.5A$ pulsed	V_{SD}		1.4	Vdc

NOTE:

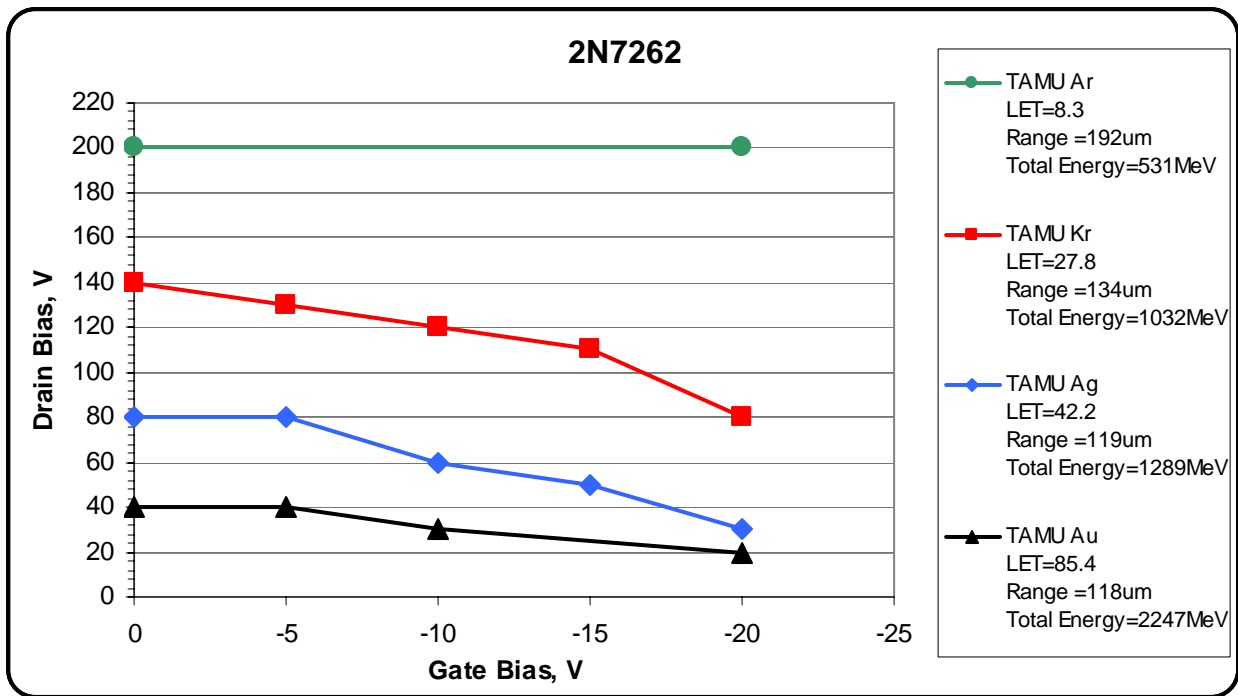
- (3) Post-Irradiation Electrical Characteristics apply to devices subjected to Steady State Total Dose Irradiation testing in accordance with MIL-STD-750 Method 1019. Separate samples are tested for VGS bias (12V), and VDS bias (160V) conditions.

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Single Event Effect (SEE) Characteristics:

Heavy Ion testing of the 2N7262 device has been characterized at the Texas A&M cyclotron. The following SOA curve has been established using the elements, LET, range, and Total Energy conditions as shown:

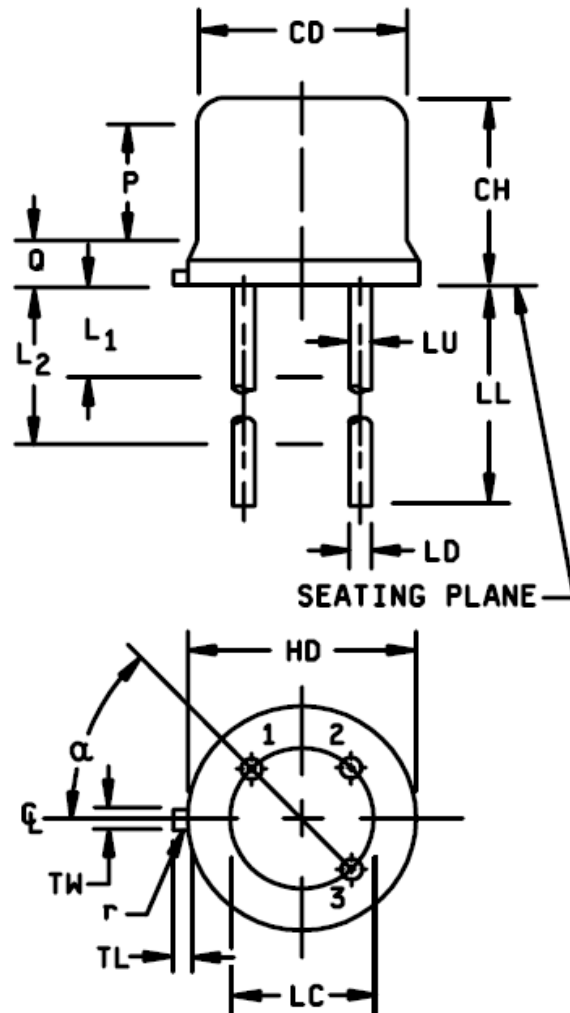


It should be noted that total energy levels are considered to be a factor in SEE characterization. Comparisons to other datasets should not be based on LET alone. Please consult factory for more information.

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Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	.315	.355	8.00	9.01
CH	.160	.180	4.07	4.57
HD	.340	.370	8.64	9.40
LC	.200 BSC		5.08 BSC	
LD	.016	.021	0.41	0.53
LL	.500	.750	12.70	19.05
LU	.016	.019	0.41	0.48
L ₁		.050		1.27
L ₂	.250		6.35	
P	.070		1.78	
Q		.050		1.27
r		.010		0.25
TL	.029	.045	0.74	1.14
TW	.028	.034	0.71	0.86
α	45° BSC			
Term 1	Source			
Term 2	Gate			
Term 3	Drain			



NOTES:

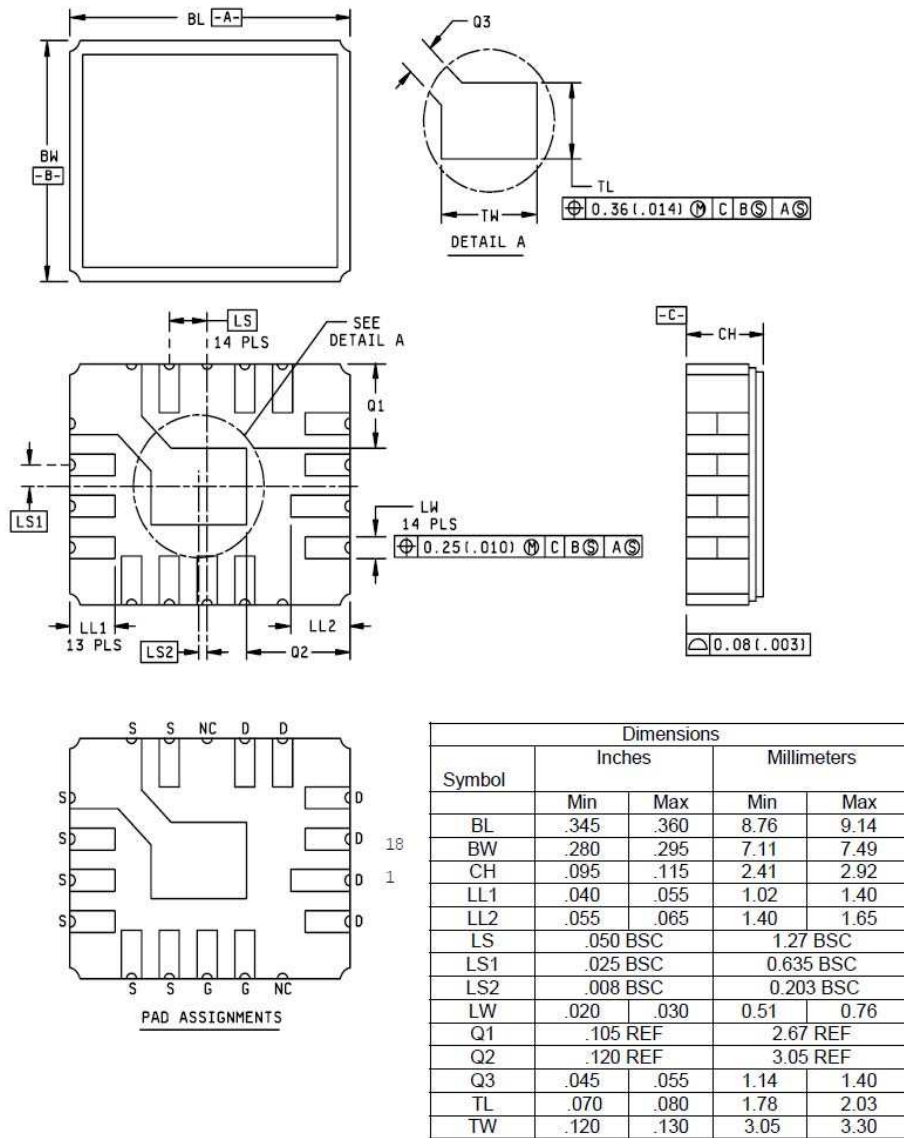
1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Lead number 1 is the source, lead number 2 is the gate, lead 3 is the drain and is electrically connected to the case, lead number 4 is omitted from this outline.
4. Dimensions and tolerancing shall be in accordance with ASME Y14.5M.

Figure 1: Case Outline and Pin Configuration for JANSR2N7262 & JANSF2N7262

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NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

Figure 2: Case Outline and Pin Configuration for JANSR2N7262U & JANSF2N7262U